



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on)	I _D T _C = +25°C
60V	7.9mΩ @ V _{GS} = 10V	69.2A
607	10.8mΩ @ V _{GS} = 4.5V	59.2A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- · Synchronous rectifiers
- DC-DC converters
- Power managements

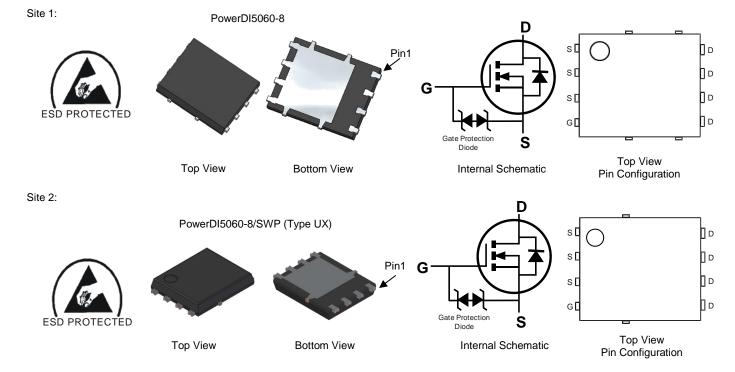
Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Rds(ON)—Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Notes:

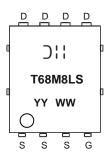


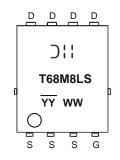
Ordering Information (Note 4)

Part Number	Pankago	Packing		
Fait Number	Package	Qty.	Carrier	
DMT68M8LPS-13	PowerDI5060-8	2500	Tape & Reel	
DMT68M8LPS-13	PowerDI5060-8/SWP (Type UX)	2500	Tape & Reel	

Notes: 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





T68M8LS = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY = Last Two Digits of Year (ex: 23 = 2023)
WW = Week Code (01 to 53)

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5) VGS = 10V	$T_A = +25$ °C $T_A = +70$ °C	lο	14.1 11.2	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		lD	69.2 55.4	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	270	Α
Maximum Continuous Body Diode Forward Current (Note 6)		Is	69	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	Ism	270	Α	
Avalanche Current, L = 0.1mH		las	28.1	Α
Avalanche Energy, L = 0.1mH		Eas	39.5	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.4	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	53	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		PD	56.8	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	2.2	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).



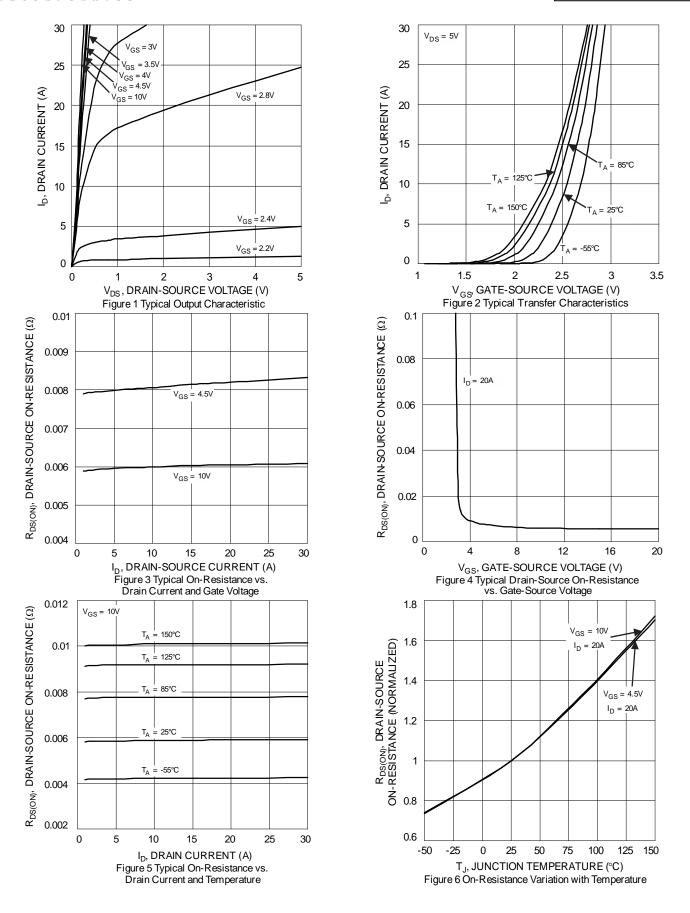
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(th)	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	D	_	5.9	7.9	mΩ	V _G S = 10V, I _D = 20A
Static Drain-Source On-Resistance	RDS(ON)	_	7.8	10.8	11177	$V_{GS} = 4.5V, I_D = 20A$
Diode Forward Voltage	VsD	_	0.7	1.2	V	$V_{GS} = 0V$, $I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	2078	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	Coss	_	605	_	pF	
Reverse Transfer Capacitance	Crss	_	44	_		
Gate Resistance	Rg	_	1.71	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	14.4	_		
Total Gate Charge (V _{GS} = 10V)	Qg		30	_	nC	V _{DS} = 30V, I _D = 20A
Gate-Source Charge	Qgs	-	4.1	_	IIC	
Gate-Drain Charge	Q_{gd}	_	6.7	_		
Turn-On Delay Time	tD(ON)	_	5.2	_		$V_{DS} = 30V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 3.3\Omega$
Turn-On Rise Time	t _R	_	9.6	_		
Turn-Off Delay Time	tD(OFF)	_	20.5	_	ns	
Turn-Off Fall Time	tF	_	8.9	_		
Reverse Recovery Time	t _{RR}	_	32.5	_	ns	I- 204 di/dt 1004/vo
Reverse Recovery Charge	Qrr	_	22.8		nC	I _F = 20A, di/dt = 100A/μs

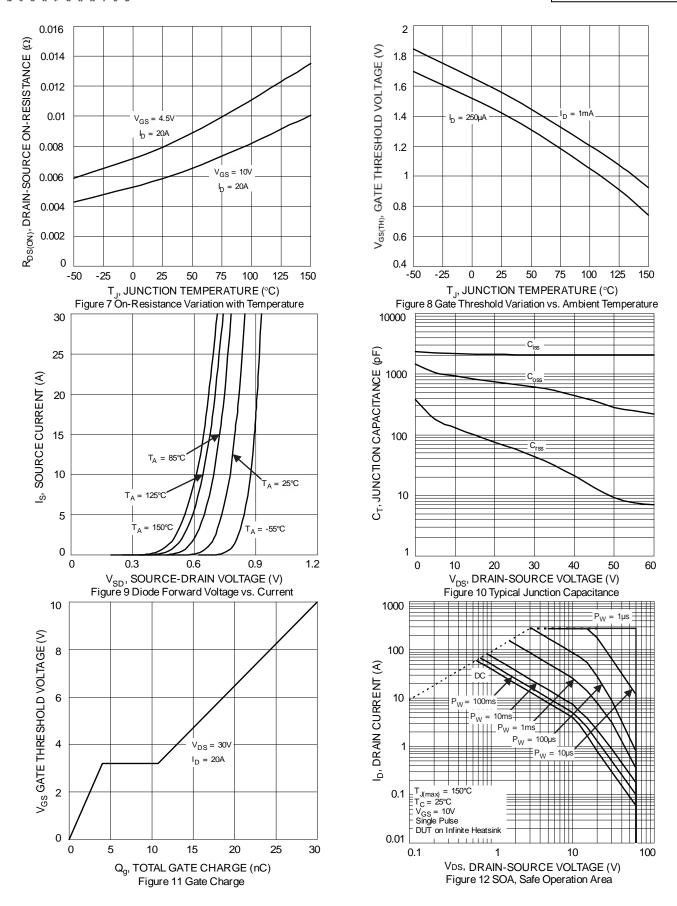
Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.

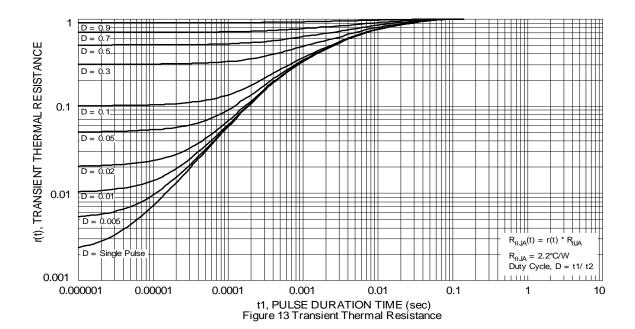












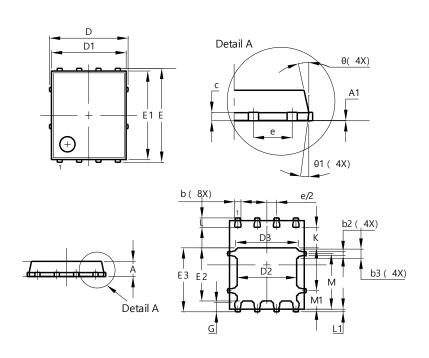


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

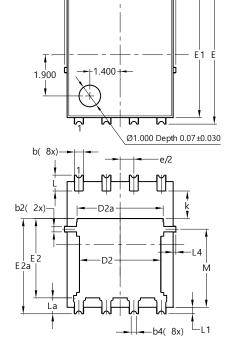
PowerDI5060-8

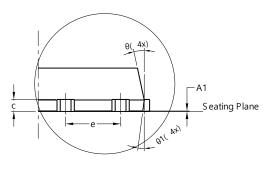


PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D		5.15 BSC		
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(6.15 BSC	;	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	1.27 BSC			
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

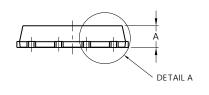
Site 2:

PowerDI5060-8/SWP (Type UX)





DETAIL A



PowerDI5060-8/SWP				
(Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A 1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4).25REF	-	
С	0.230	0.330	0.277	
D	5	.15 BS0		
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
E	6	.40 BS0		
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е		.27BSC	;	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

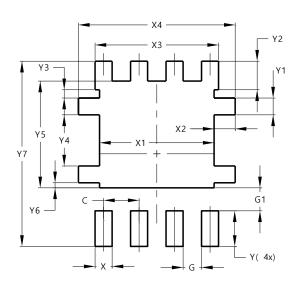


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

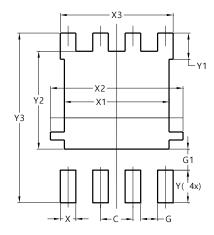
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



C 1.270 G 0.660 G1 0.820 X 0.610 X1 4.100 X2 5.190 X3 4.420 Y 1.270 Y1 1.020 Y2 3.810 Y3 6.610	Dimensions	Value		
G 0.660 G1 0.820 X 0.610 X1 4.100 X2 5.190 X3 4.420 Y 1.270 Y1 1.020 Y2 3.810	פווטופווסוטווס	(in mm)		
G1 0.820 X 0.610 X1 4.100 X2 5.190 X3 4.420 Y 1.270 Y1 1.020 Y2 3.810	С	1.270		
X 0.610 X1 4.100 X2 5.190 X3 4.420 Y 1.270 Y1 1.020 Y2 3.810	G	0.660		
X1 4.100 X2 5.190 X3 4.420 Y 1.270 Y1 1.020 Y2 3.810	G1	0.820		
X2 5.190 X3 4.420 Y 1.270 Y1 1.020 Y2 3.810	X	0.610		
X3 4.420 Y 1.270 Y1 1.020 Y2 3.810	X1	4.100		
Y 1.270 Y1 1.020 Y2 3.810	X2	5.190		
Y1 1.020 Y2 3.810	Х3	4.420		
Y2 3.810	Y	1.270		
	Y1	1.020		
Y3 6.610	Y2	3.810		
	Y3	6.610		



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